#### Montanuniversität Leoben

## Sputtered polymeric hydrogenated amorphous carbon thin films for temporary medical implants

Gesputterte polymerartige amorphe hydrogenisierte Kohlenstoffschichten für temporäre medizinische Implantate

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Leoben, March 2013

# **Affidavit** I declare in lieu of oath that I did the diploma thesis by myself using only literature cited in this work. Talkofer Julia Leoben, March 2013

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#### **ABBREVIATIONS**

a-C ... amorphous carbon

a-C:H ... hydrogenated amorphous carbon

Ar ... argon

Ar+ ... argon ions

C ... carbon

C<sub>2</sub>H<sub>2</sub> ... acetylene

 $(CH_2)_n$  ... methylene

CAE ... Constant Analyzer Energy

CBMS ... Conventional Balanced Magnetron Sputtering

D ... disordered

DC ... Direct Current

DLC ... diamond-like carbon

ERDA ... Elastic Recoil Detection Analysis

FIB ... Focused Ion Beam

FWHM (G) ... full width at half maximum of the G-band

G ... graphite

H ... hydrogen

 $I_D/I_G$  ... Intensity ratio

 $I_m \quad ... \quad current \ at \ magnetron$ 

Is ... current at substrate holder

N ... nitrogen

0 ... oxygen

PECVD ... Plasma-Enhanced Chemical Vapour Deposition

P<sub>m</sub> ... power at magnetron

PVD ... Physical Vapour Deposition

RBS ... Rutherford Backscattering Spectroscopy

SEM ... Scanning Electron Microscope

Si ... silicon

ta-C ... tetrahedral amorphous carbon

ta-C:H ... tetrahedral hydrogenated amorphous carbon

TEM ... Transmission Electron Microscopy

UBMS ... Unbalanced Magnetron Sputtering

U<sub>m</sub> ... potential at magnetron

U<sub>s</sub> ... potential at substrate holder

XPS ... X-Ray Photoelectron Spectroscopy

XRD ... X-Ray Diffraction

Z ... atomic number

#### 1 Introduction

### "Thin-film technology is simultaneously one of the oldest arts and one of the newest sciences" - Milton Ohring

Presently, temporary metallic implants, like bone nails, based on stainless steel and titanium are widely employed. One of the major deficiencies of these implants is that they have to be removed operatively after fulfilling their task, e.g. after healing of fractured bones.

Hence, recently there are reflections about bio-degradable implants based on magnesium. They convince not only with their biocompatibility, low weight and sufficient load-bearing capacity, but also with their elastic properties closely resembling those of human bones [1]. Furthermore, magnesium is absorbed and degraded completely by the physiological environment after gradual depletion. This bio-degradation is based on corrosion of magnesium in aqueous environment, but it results in considerable gas accumulations in the surrounding tissue and injures the same [2].

The aim of this work is to provide a feasibility study on the design and development of a multifunctional coating system based on hydrogenated amorphous carbon, which is biocompatible, smooth, tough and soft. The task of this coating system is on the one hand to prevent the implant from corrosion during the healing process. On the other hand, a slow degradation of the film, which should ensure controlled access of water to the magnesium surface due to a specific porosity, should provide for a controlled degradation of the implant.

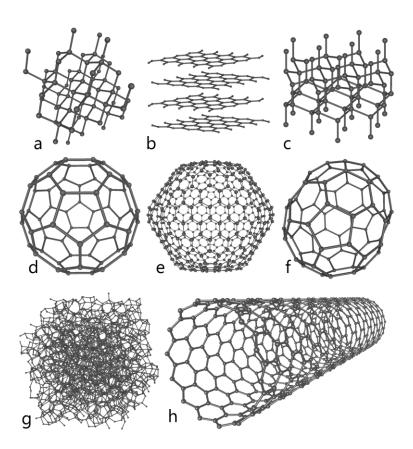
The coatings were synthesised by reactive magnetron sputtering of a graphite target in an argon/acetylene atmosphere. The basic correlations between deposition parameters, coating structure and mechanical coating properties should be accomplished.

#### 2 BACKGROUND INFORMATION

#### 2.1 Almost everything about Carbon

#### 2.1.1 Structure and Properties

Carbon compounds form the molecular basis of all terrestrial life, consequently carbon is very biocompatible. It is a member of the main group 4 of the periodic table, has the atomic number 6 and the symbol C. It is non-metallic and tetravalent, which means it has four electrons to form covalent chemical bonds. There are eight allotropes (Figure 2.1) of carbon, where the best known are graphite, diamond and amorphous carbon. The physical properties of carbon vary widely with the allotropic form. This shows up for example in the appearance, where graphite is opaque and diamond is transparent. While graphite is soft enough to write on a paper, diamond is known as the hardest naturally-occurring material. On the other hand, graphite is a good conductor while diamond has a low electrical conductivity.



**Figure 2.1:** Allotropes of carbon: (a) diamond, (b) graphite, (c) ionsdaleite, (d)-(f) fullerenes ( $C_{60}$ ,  $C_{540}$ ,  $C_{70}$ ), (g) amorphous carbon and (h) carbon nanotube [3].

Due to its special electronic configuration (L-shell half filled), carbon possesses the ability to form complex molecules and shows the greatest variety of chemical compounds. The enormous versatility of the carbon material system is based on the different bond hybridisations, i.e. sp<sup>3</sup>, sp<sup>2</sup> and sp<sup>1</sup>, as shown in Figure 2.2.

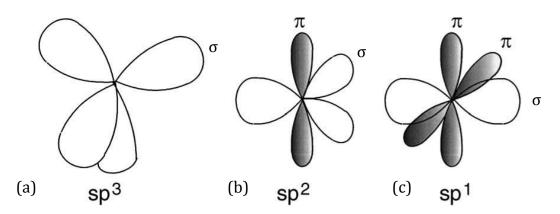


Figure 2.2: The three bond hybridisations found in carbon: sp<sup>3</sup>, sp<sup>2</sup> and sp<sup>1</sup> [4].

The metastable sp<sup>3</sup> configuration, as in diamond, is a fully tetrahedral C-C bonding formation (Figure 2.2 (a)). Diamonds are not only a girl's best friend but have a very powerful image in the public and scientific community. It has the largest bulk modulus of any solid, the highest atom density, the largest room temperature thermal conductivity (900-2300 W m<sup>-1</sup> K<sup>-1</sup>), the smallest thermal expansion coefficient (0.8  $\mu$ m m<sup>-1</sup> K<sup>-1</sup>), and an optical gap of 5.5 eV due to four strong  $\sigma$  bonds (covalent bonds) at 109.5° to each other [5].

Graphite is characterised by a fully trigonal  $sp^2$  network that forms planar six-fold rings of single and double bonds, with weak van der Waals  $\pi$  bonds between the planes of its hexagonal structure. Concerning the highly delocalised  $\pi$  electrons along the 'c' axis (Figure 2.2 (b)), graphite has a band gap of zero [5].

The sp<sup>1</sup> bond consists of two strong  $\sigma$  orbitals along the x-axis and two further p $\pi$  orbitals in the y and z directions (Figure 2.2 (c)).

Diamond-like carbon (DLC) in general is a mixture of  $sp^3$ ,  $sp^2$  and  $sp^1$  sites. DLC is an amorphous carbon (a-C) or hydrogenated amorphous carbon (a-C:H) thin film material with a high fraction (20-60%) of metastable  $sp^3$  carbon bonding [6]. It is generally prepared by a deposition process involving energetic ions. The metastable  $sp^3$  bonds transform to  $sp^2$  under thermal or mechanical loads. DLC can have

different properties like high mechanical hardness, chemical inertness, optical transparency and a relatively wide band gap.

DLC is much less "famous" compared to diamond, but not less important than diamonds in economic terms. These coatings are used on very different applications like razor blades, in magnetic hard-disk drives, on bar-code scanners, on PET bottles, on some car parts and on medical devices.

#### 2.1.2 Phase Diagram

The different carbon phases can be displayed in a ternary phase diagram shown in Figure 2.3. The phase diagram was first established by Jacob and Moller [7] and illustrates the fraction of sites in the C-matrix that are C sp<sup>3</sup>, C sp<sup>2</sup> or hydrogen (H).

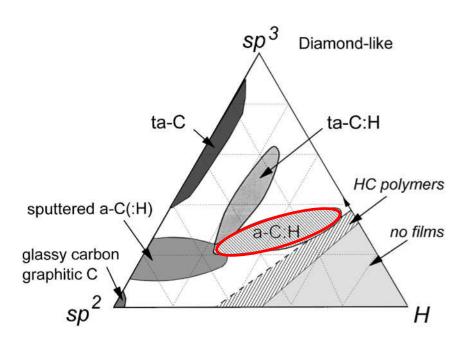


Figure 2.3: Ternary phase diagram of the C-H system [7].

Three main sections in this ternary phase diagram can be distinguished. Along the sp<sup>2</sup>-sp<sup>3</sup> axis there is the H-free a-C region. The sp<sup>2</sup> a-C is characteristically glassy carbon and not DLC and is made by evaporation or by pyrolysis of hydrocarbon polymers.

Sputtered DLCs with quite large sp<sup>3</sup> content, still without H, can be prepared for example with unbalanced magnetron sputtering [8]. If the sp<sup>3</sup> content further increases, there is a specific type of a-C called tetrahedral amorphous carbon (ta-C). Due to its high sp<sup>3</sup> content, the properties are more like diamond than graphite.

In the hydrogen rich corner the compounds have gaseous nature [7].

The boundary line of this second region is defined by the compositions of acetylene  $(C_2H_2)$  on the  $sp^2$ -H axis and methylene  $((CH_2)_n)$  on the  $sp^3$ -H axis. The a-C:H materials are situated within these regions. They can be produced by reactive sputtering of graphite in a hydrogen-containing atmosphere, by plasma-enhanced chemical vapour deposition (PECVD) of hydrocarbon molecules, or by ion beam deposition from a hydrocarbon gas precursor. These a-C:H films can have H contents from 20 up to 60% [8] and compared with ta-C they are polymeric, softer and tougher.

With so-called high-density plasmas, denser a-C:H films can be produced called tetrahedral hydrogenated amorphous carbon (ta-C:H).

DLC has some extreme properties similar to diamond, like hardness, elastic modulus and chemical inertness. Apart from that, it forms isotropic disordered thin films without grain boundaries [6].

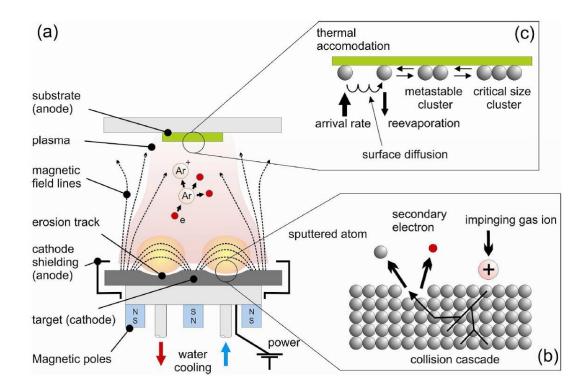
#### 2.2 Deposition Technique – Sputtering

#### 2.2.1 Fundamentals of Sputtering

Sputtering is a vacuum process where incident inert gas ions, usually Ar<sup>+</sup> ions, eject atoms or clusters from a solid target material which transfer into a gaseous phase due to momentum transfer. These positive ions are generated in a glow-discharge ignited between two electrodes, where the target is the cathode and the substrate holder or the chamber wall forms the anode (Figure 2.4 (a)).

The incident gas ion transfers its impulse to the target atoms, which trigger further collisions like a shock cascade. After several collisions some of the momentum point towards the surface. Atoms knocked on by this momentum may leave the target if they have enough energy and if they are near the surface (Figure 2.4 (b)). The ejected atoms condense on the substrate that is positioned near the target (Figure 2.4 (c)).

Sputtering is done in vacuum in the pressure range of  $10^{-3}$  -  $10^{-2}$  mbar to reduce the collision probability of sputtered species with gas atoms.



**Figure 2.4:** (a) Schematic illustration of a magnetron sputtering system showing the most relevant processes during (b) a sputter procedure at the target and (c) the nucleation process at the sample surface [9].

Generally a direct current (DC) gas discharge serves as an ion source. The target acts as negative (cathode) and the substrate as positive electrode (anode). If there is a permanent magnetic field beneath the target, the so-called magnetron sputtering can be put into practice. It can be categorised into two types:

- conventional balanced magnetron sputtering (CBMS) and
- unbalanced magnetron sputtering (UBMS).

In CBMS, all magnetic field lines are closed between the poles. In UBMS, the field lines are partially open towards the substrate. It is realised by using stronger outer or inner magnets. Figure 2.5 illustrates schematic diagrams of CBMS and UBMS processes.

Due to the interaction between the electric and magnetic field, the charge carriers move in spirals instead of parallel so that they circulate above the target surface. As a result their way extends and the number of collisions per electron rises.

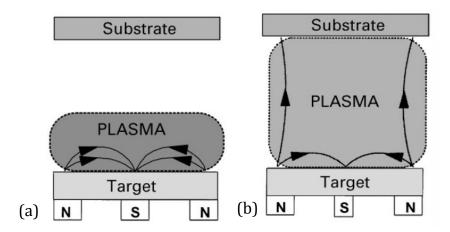


Figure 2.5: Schematic illustration of (a) a balanced and (b) an unbalanced magnetron [10].

#### 2.2.2 Reactive Sputtering

In general, to produce alloys or compounds reactive sputtering is a common technique besides sputtering with multicomponent or different single element targets. There, at least one component of the film originates from the gas phase. Additionally to the inert working gas, for example argon, a particular fraction of reactive gas, for example acetylene ( $C_2H_2$ ) or nitrogen ( $N_2$ ), is introduced into the vacuum chamber.

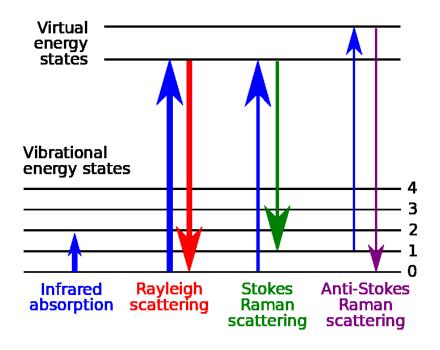
Three different reactions are possible to form the compound [11] [12]:

- The compound is formed at the target surface and these molecules are sputtered.
- The compound is formed in the gas phase.
- The reactive gas is adsorbed on the substrate and subsequently there is a reaction with the impinging target atoms.

Whereas the compounds formed at the target surface are estimated to be sputtered as single atoms and due to the low probability of collisions between sputtered atoms, reactive gas molecules and ions/electrons in the gas phase, the third reaction is the most important one. An advantage of reactive sputtering is that with modifying the partial pressure of the reactive gas, the stoichiometry of the resulting film can be adjusted. By employing simple metallic targets and providing several components in the gas phase, even very complex films can be produced [13].

#### 2.3 Raman Spectroscopy

The Raman effect was first described by Chandrasekhara Venkata Raman [14]. It is based on inelastic scattering of monochromatic light, usually from a laser in the visible, near infrared or near ultraviolet range, with phonons or other excitations in the atomic system (Figure 2.6) to estimate for example phase composition, crystallinity or stresses.



**Figure 2.6:** Photon-phonon interaction in Raman spectroscopy [15].

The energy of the laser photons is shifted up or down and this shift gives information about the phonon modes in the system. Raman spectroscopy is known to be the most convenient method of bonding structure investigations of carbon materials. Each configuration of carbon has its own typical Raman spectra, as shown in Figure 2.7. Diamond and single crystalline graphite have single Raman active modes at 1332 cm<sup>-1</sup> and 1580 cm<sup>-1</sup>, respectively. In single crystalline graphite, the mode is labelled 'G' for 'graphite'. The G-mode is the stretching vibration of any pair of sp<sup>2</sup> sites, no matter if in chains or aromatic rings [16]. Disordered graphite, like DLC, has a second mode at about 1350 cm<sup>-1</sup> labelled 'D' for 'disordered', which is the breathing mode of the sp<sup>2</sup> sites just in rings, not in chains (Figure 2.8). In single crystalline graphite this mode is forbidden [16].

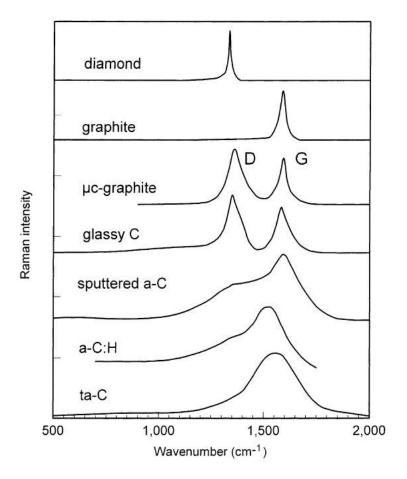


Figure 2.7: Comparison of different carbon Raman spectra [6].

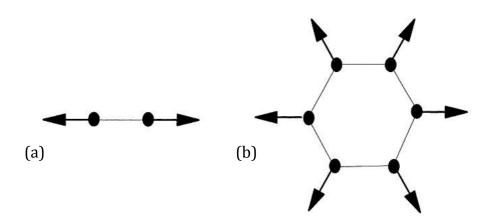
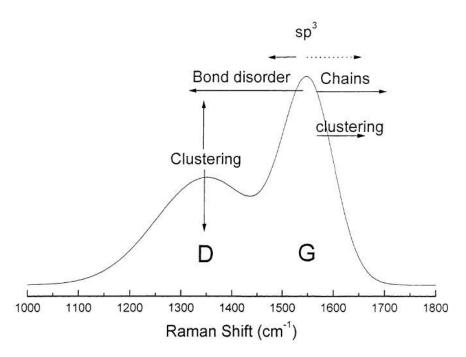


Figure 2.8: (a) G mode in graphite and (b) D mode in amorphous carbon [16].

These G and D modes dominate the Raman spectra of each disordered graphite film. Various factors as shown in Figure 2.9 can shift the peaks in either direction and vary their relative intensity.



**Figure 2.9:** Schematic Raman spectrum of amorphous carbon showing the factors affecting the position and height of G and D peak [16].

Before analysing the Raman spectra it is important to know which method has been used to fit the spectra because this influences the numerical values. In this work, the spectra were fitted with a Gaussian distribution function (Figure 2.10). In a Gaussian fit, the areas of the fitted D- and G-band are used for estimating the intensity ratio  $I_D/I_G$ .

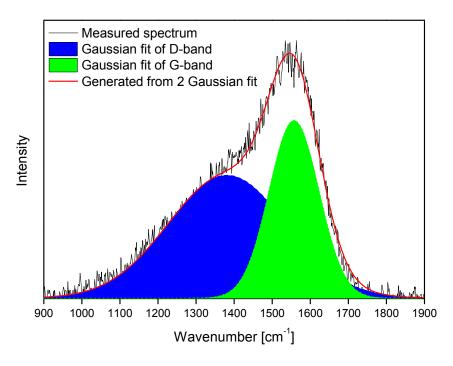


Figure 2.10: Gaussian fit of D- and G- band [own work].

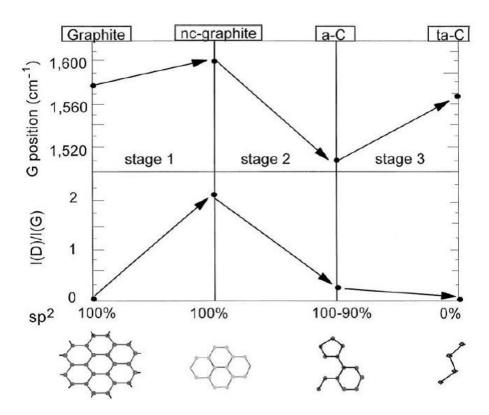
The Raman spectrum of a-C is sp<sup>2</sup> site dominated and according to this there is no direct information about the sp<sup>3</sup> bonding fraction via visible light excitation.

Investigations of the  $I_D/I_G$  ratio of the considered disorder structure show an indirect correlation. Due to the fact that the  $sp^2$  site disorder is influenced by the  $sp^3$  fraction, the  $I_D/I_G$  ratio can be inversely used to get information about the  $sp^3$  fraction existing in the a-C phase [6] [17]. Hence, the  $sp^2$  fraction can be gauged by the hybridisation ratio:

$$\frac{I_D}{I_G} \sim sp^2 \sim \frac{1}{sp^3} \tag{1}$$

Ferrari and Robertson [16] suggested classifying all Raman spectra of disordered carbon within a three-stage model of increasing disorder. In Figure 2.11 these three stages are shown.

- 1. perfect graphite to nano-crystalline graphite
- 2. nano-crystalline graphite to a-C
- 3. a-C to ta-C



**Figure 2.11:** Schematic trajectory of the Raman G peak wavenumber and  $I_D/I_G$  ratio with degree of disorder [adapted from [16]].

**Stage 1** is in accordance with the structural change from perfect graphite to nanocrystalline graphite with the following main changes in the Raman spectra [16]:

- The G-band moves from 1580 to  $\sim$ 1600 cm-1.
- The D-band appears and the intensity ratio ID/IG increases.

Reference [16] explains these variations in detail.

**Stage 2** corresponds to the structural change from nano-crystalline graphite to a-C and at the end of this stage, there is a completely disordered, almost fully sp<sup>2</sup> bonded a-C network consisting of distorted six-fold rings or rings of other orders [16]. The main changes in the Raman spectra are [16]:

- The G-band moves from  $\sim$ 1600 to 1510 cm-1.
- The intensity ratio ID/IG decreases, which means a decrease of the number of ordered sp<sup>2</sup> rings.

**Stage 3** is equivalent to the structural change from a-C to ta-C, which means the sp<sup>3</sup> content increases from  $\sim 10$  to  $\sim 85\%$  [16] and the sp<sup>2</sup> sites change successively from rings to chains. The main changes in the Raman spectra are [16]:

- The G-band moves from  $\sim$ 1510 to 1570cm-1.
- The intensity ratio ID/IG decreases nearly to zero.

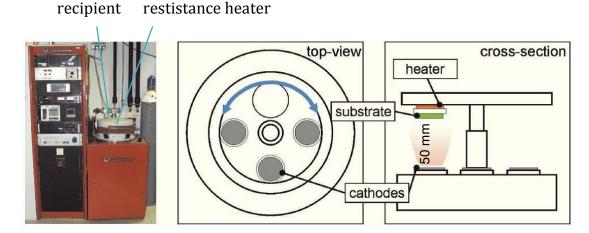
This structural evolution through these three stages is called amorphisation trajectory or disordering trajectory, whereas in the reverse direction it is called ordering trajectory.

#### 3 EXPERIMENTAL METHODS

#### 3.1 Sputter Deposition

#### 3.1.1 Deposition System

All coatings for this work were deposited using a modified Leybold-Heraeus Z 400 DC reactive unbalanced magnetron sputtering device, as schematically shown in Figure 3.1 [18] [19].



**Figure 3.1:** Schematic construction of the deposition chamber [9].

The sputtering system consists of a cylindrical recipient ( $\varnothing$  420 mm × 200 mm), which contains space for three water cooled magnetrons. The magnetrons are horizontally fixed and for this thesis just one carbon target ( $\varnothing$  75 mm × 6 mm) was situated on one magnetron and the other two were covered.

The substrate holder is mounted on a horizontal rotary device at a distance of  $\sim 50 \text{ mm}$  from the target. For the sputtering process it is positioned above the magnetron.

The discharge is ignited between the magnetron and the substrate holder. An MKS ENI RPG-50 pulsed DC power supply (frequency 250 kHz, duty cycle of 496 ns – 40%) was applied for plasma etching of the substrates by using a negative bias voltage of -500 V. After etching the bias voltage was reduced to -50 V during deposition. A modified Leybold-Heraeus power supply was used to provide the magnetron with a maximum power of 2 kW. For the required vacuum inside the deposition chamber, a dual stage rotary vane pump (Pfeiffer DUO 20, [20]) and a

turbomolecular pump (Leybold Turbovac 361, [21]) were utilised. Furthermore, outside the recipient a resistance heater was attached to bake out the chamber. A residual pressure of less than  $2 \times 10^{-5}$  mbar was reached.

#### 3.1.2 Calibration of the Sputter System

In order to estimate the gas pressure for deposition, two calibration runs were done. The first one, shown in Figure 3.2, was done for the working gas (argon) for a flow rate from zero to 40 sccm. For argon a correction factor of 0.83 has to be considered [19], which shows up in the corrected chamber pressure.

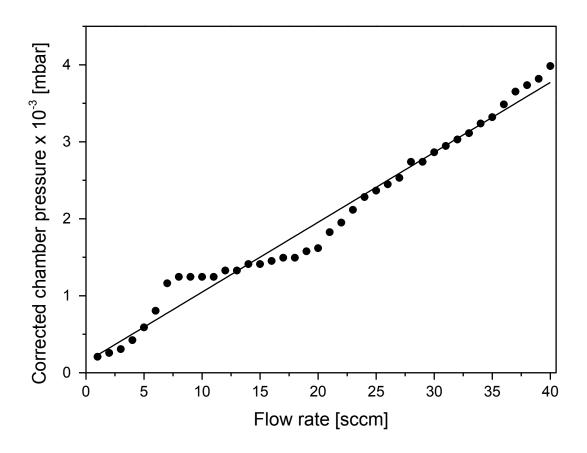
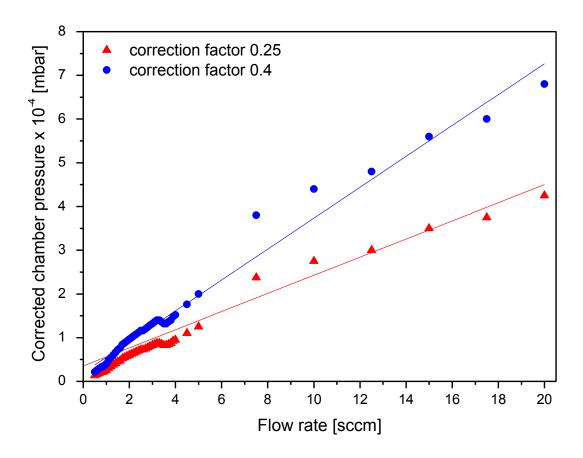


Figure 3.2: Corrected flow rate of the working gas (argon).

The second calibration run, shown in Figure 3.3, was done for the reactive gas  $(C_2H_2)$  for a flow rate from zero to 20 sccm. For this hydrocarbon, the correction factor is between 0.1 and 0.4 [19].



**Figure 3.3:** Corrected flow rate of the reactive gas  $(C_2H_2)$  calibrated with two different correction factors.

These calibration curves are important for the deposition process, because every gas has its own partial pressure and contributes to the total pressure with different amount due to the prevalent gas mixture.

#### 3.1.3 Sputter Procedure

All variants of the coating were deposited on Si (100) (20 mm  $\times$  7 mm  $\times$  0.380 mm) wafers. Prior to deposition, the substrates were ultrasonically cleaned in acetone and ethanol for 5 min each and dried by a hot air gun.

For further substrate cleaning, they were plasma etched for 15 min after evacuating the chamber to a total pressure of less than  $1 \times 10^{-5}$  mbar. For plasma etching, the Ar (99.999% purity) gas flow was set to 40 sccm, which lead to a total pressure increase up to  $10^{-2}$  mbar. A negative bias voltage of -500 V was applied to force collisions of the Ar<sup>+</sup> ions with the substrate surface. After etching, the Ar gas flow was turned off and the chamber was evacuated to a total pressure below  $4 \times 10^{-6}$  mbar again.

All deposition runs were carried out for 30 minutes. No external heating of the substrate holder was used resulting in an estimated temperature of  $200^{\circ}$ C. The gas flow of Ar (working gas) was kept constant at 10 sccm for all depositions and the  $C_2H_2$  (reactive gas) gas flow gradually increased from 0 to 10 sccm, resulting in a partial pressure variation as shown in Figure 3.2 and Figure 3.3. After deposition the chamber was cooled down for one hour with a resulting total pressure of about  $4 \times 10^{-6}$  mbar. Table 3.1 shows the deposition parameters of all runs.

**Table 3.1:** Deposition parameters

| Sample<br>name | flow<br>(Ar) | flow<br>(C <sub>2</sub> H <sub>2</sub> ) | total<br>pressure      | BIAS U <sub>s</sub> | BIAS I <sub>s</sub> | P <sub>m</sub> | Um  | I <sub>m</sub> |
|----------------|--------------|--|------------------------|---------------------|---------------------|----------------|-----|----------------|
|                | [sccm]       | [sccm]                                   | [mbar]                 | [V]                 | [mA]                | [W]            | [V] | [mA]           |
| аСН-0          | 10           | 0  | 8.1 × 10 <sup>-3</sup> | -50                 | 80                  | 400            | 595 | 610            |
| аСН-2          | 10           | 2  | 1.1 × 10 <sup>-2</sup> | -50                 | 80                  | 400            | 553 | 670            |
| аСН-4          | 10           | 4  | 1.4 × 10 <sup>-2</sup> | -50                 | 80                  | 400            | 532 | 700            |
| аСН-6          | 10           | 6  | 1.7 × 10 <sup>-2</sup> | -50                 | 80                  | 400            | 517 | 730            |
| аСН-8          | 10           | 8  | 2.0 × 10 <sup>-2</sup> | -50                 | 80                  | 400            | 539 | 690            |
| aCH-10         | 10           | 10                                       | 2.2 × 10 <sup>-2</sup> | -50                 | 80                  | 400            | 616 | 670            |

#### 3.2 Coating Characterisation

#### 3.2.1 Coating Thickness

The coating thickness *d* was measured at the Materials Center Leoben with a scanning electron microscope (SEM, Zeiss SMT Auriga) by cutting into the sample (Figure 3.4) with a focused ion beam (FIB, Orsay Physiks Cobra Z-05).

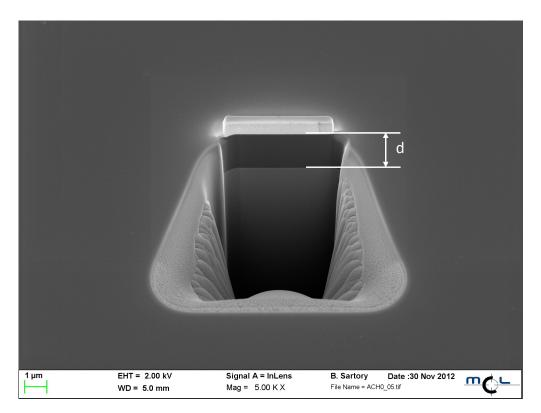


Figure 3.4: FIB cut for coating thickness measurement.

#### 3.2.2 Elastic Recoil Detection Analysis (ERDA)

ERDA is deemed to be the most convenient method to determine the hydrogen content in DLC films. L'Ecuyer et al. first established the formalism for this determination in 1976 [22]. It is based on the detection of light nucleus recoil from a target bombarded by energetic ions [23]. The energy of a recoil nucleus  $E_1$  is defined through the following equation [23]:

$$E_1 = E_0 \frac{4M_1 M_2}{(M_1 + M_2)^2} \cos^2 \theta \tag{2}$$

There,  $E_0$  is the projectile particle initial energy,  $M_1$  and  $M_2$  are the masses of the projectile and the target atom and  $\theta$  is the recoil angle. In Figure 3.5 the collision between an incident ion  $M_1$  and a target atom  $M_2$  is schematically shown.

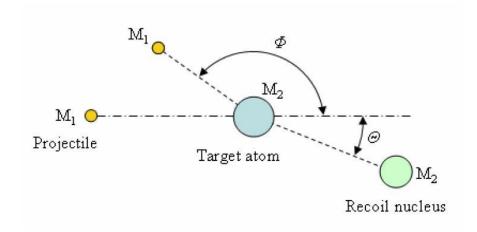


Figure 3.5: Schematic collision process [adapted from [23]].

The relation between the scattering angle  $\phi$  (RBS) and the recoil angle  $\theta$  (ERDA) characterises the geometry of the collision [23]:

$$\cos^2 \theta = \frac{(M_1 M_2)^2 - (M_1 \cos \phi \pm \sqrt{M_2^2 - M_1^2 \sin^2 \phi}))^2}{4M_1 M_2}$$
(3)

In this work, ERDA measurements were carried out at the Helmholtz-Centre Dresden-Rossendorf using a 35 MeV  $Cl^{7+}$  ion beam. The angle between the sample normal and the incoming beam was set to 75°, the scattering angle was set to 31°. The analysed area was about  $1.5 \times 1.5$  mm². The recoil ions have been detected with a Bragg ionisation chamber using a full energy detection circuit for the ion energies and a fast timing circuit to obtain a Z (atomic number) dependent signal to separate ion species. H has been detected with a separate solid state detector at a scattering angle of 41° preceded by an 18  $\mu$ m Al foil to stop other scattered and recoiled ions.

#### 3.2.3 X-Ray Diffraction (XRD)

The measurements were carried out with a Bruker-AXS D8 Advance diffractometer using Cu K $\alpha$  radiation. The detector scan mode with a grazing incidence angle of 2° and a 2 $\theta$  angle between 10 and 100° was used. The operating parameters shown in Table 3.2 were kept constant for all measurements.

**Table 3.2:** Operating parameters of the Bruker-AXS D8 Advance diffractometer.

| High Voltage | Tube Current | Step Time | Step Size 2θ |  |
|--------------|--------------|-----------|--------------|--|
| [kV]         | [mA]         | [s]       | [°]          |  |
| 40           | 40           | 1.2       | 0.02         |  |

#### 3.2.4 X-Ray Photoelectron Spectroscopy (XPS)

With XPS the elemental composition as well as the chemical and electronic state of elements within a material can be determined. The material is irradiated with a X-ray beam while simultaneously the kinetic energy and number of electrons escaping is measured. In this work, XPS was used to determine the contribution of the binding energy  $E_B$  of the C1s orbital of carbon, which gives information about the sp<sup>2</sup> and sp<sup>3</sup> content:

$$E_B = E_{Ph} - (E_K + \phi) \tag{4}$$

There,  $E_B$  is the binding energy of the electron,  $E_{Ph}$  is the known energy of the X-ray photons (composed of hv; with h as Planck's constant and v as radiation frequency),  $E_K$  is the kinetic energy of the electron as measured by the instrument and  $\phi$  is the work function of the spectrometer.

Within this work, the measurements were carried out at the Chair of Chemistry of Polymeric Materials at the Montanuniversität Leoben with a Thermo Scientific K-Alpha X-ray Photoelectron Spectrometer. The parameters are listed in Table 3.3.

**Table 3.3:** Used acquisition parameters for XPS.

| No. Scans | Source Type | Spot Size | Lens<br>Mode | Analyser<br>Mode             | Energy<br>Step Size |
|-----------|-------------|-----------|--------------|------------------------------|---------------------|
|           |             | [µm]      |              |                              | [eV]                |
| 3         | ΑΙ Κα       | 400       | Standard     | CAE : Pass<br>Energy 50.0 eV | 0.1                 |

#### 3.2.5 Raman Spectroscopy

In this work Raman spectroscopy was used to determine the ratio of  $I_D/I_G$ , which means to estimate the ratio of  $sp^2/sp^3$  content of the films. The measurements were carried out by using a Horiba Dilor Raman spectroscope with a laser wavelength of 532.2 nm (Nd:YAG laser) at a power level of 100 mW (3.5 mW at the measurement point). Different filters were used to reduce the intensity of the laser to avoid damaging of the film. The recorded data were fitted with the Gaussian method and compared with literature.

#### 3.2.6 Nanoindentation

The hardness and Young's modulus were quantified with a Nanoindentor System (UMIS, Fischer-Cripps Laboratories). All measurements were carried out with a Berkovich diamond tip with a tip radius less than 200 nm. In literature the indentation depth is commonly controlled to the  $\leq 1/10$  rule of thumb for hardness measurements [24]. A test series with decreasing load starting at 10 mN and a step size of 1 mN was done.

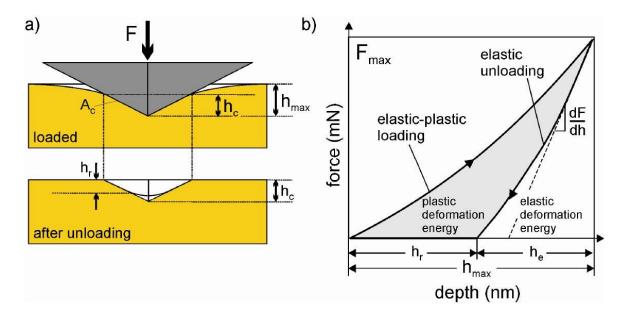
Two essential conditions have to be considered for meaningful measurements:

- no appreciable substrate influence
- a fully-developed plastic zone below the indent.

The hardness was calculated on the basis of the load-displacement curve (Figure 3.6):

$$H = \frac{P}{A} * \frac{A_i}{A} \tag{5}$$

There, P is the indentation load, A is the contact area and  $\frac{A_i}{A}$  is the area function, which is used to correct a not exactly sharp tip.



**Figure 3.6:** a) Schematic illustration of an indentation and b) a typical load-displacement curve showing elastic and plastic contributions [25].

The Young's modulus was calculated by the method of Oliver and Pharr [26]:

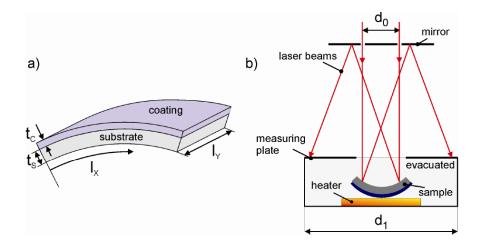
$$E^* = \frac{dP}{dh} \frac{\sqrt{\pi}}{2\beta\sqrt{A}} \sqrt{\frac{A_i}{A}}$$
 (6)

There, dh is the indentation depth,  $\frac{dP}{dh}$  is the stiffness of the material and  $\beta$  is the indenter geometry factor.

#### 3.2.7 Residual Stresses

After deposition, there are intrinsic and thermal stresses in the film. Consequently, the coated substrate bends (Figure 3.7 (a)) and can cause failure like delamination of the film. Stresses can be determined by measuring the curvature of the surface.

In this thesis, a laser based optical testing method was used to determine the stress levels at room temperature and enhanced temperatures [27].



**Figure 3.7:** a) Schematic illustration of a curved substrate/coating composite due to residual stresses and b) laser based biaxial stress measurement with parallel laser beams [adapted from [27]].

The samples were positioned in a vacuum chamber to ensure stable measurement conditions. Subsequently, the chamber was evacuated to a total pressure of  $5 \times 10^{-5}$  mbar. The measurement started at room temperature and went up to  $700^{\circ}$ C in steps of  $50^{\circ}$ C. To measure the curvature of the surface due to internal stress, two parallel He-Ne-laser beams ( $\lambda$ =632.8 nm, beam diameter: 1.2 mm) were used, which were first reflected from the sample surface and then from a mirror (Figure 3.7 (b)). These beams were projected to a white surface where they are detectable as two points. The distance of these points was measured both during heating and cooling and is proportional to the radius of curvature of the sample. The radius of curvature R of the coated silicon substrates was calculated with:

$$R = \frac{2hd_0}{d_1 - d_0} \tag{7}$$

There, h is the distance between film surface and mirror,  $d_{\theta}$  is the initial distance between the two laser beams and  $d_{1}$  is the measured distance after reflection, see Figure 3.7. For the calculation of the nominal stress  $\sigma_{f}$ , the modified Stoney formula was used:

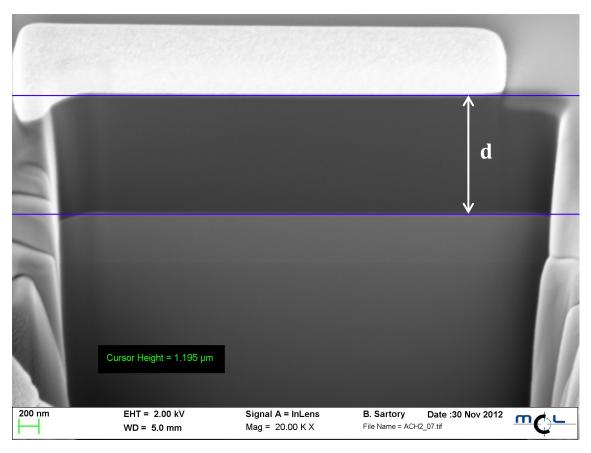
$$\sigma_f = M \frac{t_s^2}{6t_c} \frac{1}{R} \tag{8}$$

There, M is the biaxial modulus of the substrate,  $t_s$  is the thickness of the substrate,  $t_c$  is the thickness of the coating and R is the radius of curvature of the substrate [27].

#### 4 RESULTS

#### 4.1 Coating Thickness

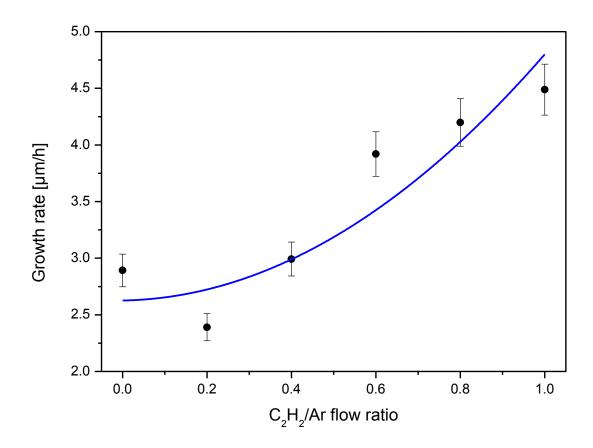
Figure 4.1 illustrates a representative FIB cut, showing substrate (grey) and coating (dark grey), where the coating thickness d was measured. The micrograph indicates good adhesion between substrate and coating without any cracks. The film appears dense without pores or holes, it shows an amorphous structure with uniform thickness and smooth surface (see also the lower magnification micrograph in Figure 3.4).



**Figure 4.1:** FIB cut for measuring the coating thickness (sample aCH-2).

The measured film thicknesses increase from 1.4 (without  $C_2H_2$ ) to 2.2  $\mu$ m (with  $C_2H_2$ /Ar flow ratio of 1.0), which results in a film growth rate from about 2.5 up to nearly 5.0  $\mu$ m per hour. Figure 4.2 shows this increase of the growth rate due to an

increasing  $C_2H_2/Ar$  flow ratio. Up to a flow ratio of 0.4, the growth rate seems to be nearly constant. But above, the reactive gas contributes significantly to the film growth, resulting in considerably higher growth rates [28]. The standard deviation of 5% is due to calculated measuring inaccuracy.



**Figure 4.2:** Film growth rate as a function of the  $C_2H_2/Ar$  flow ratio.

#### 4.2 Elastic Recoil Detection Analysis

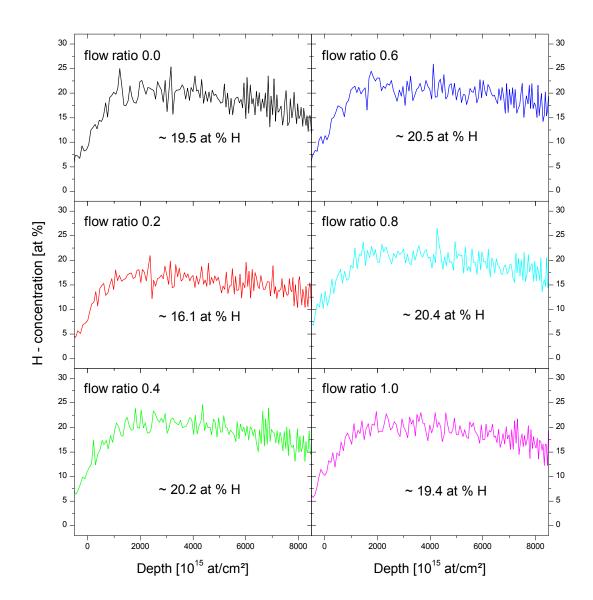
The results of the ERDA measurements for all samples are summarised in Table 4.1. All coatings have an average H-content of 20 at %. The contamination of oxygen is below 0.3 at % and for nitrogen it is between 0.3 and 0.9 at %. The relatively low content of contamination indicates a constant overall condition of the deposition system without any leaks. The coating with a flow ratio of 0.2 shows a slightly lower H-content of 16 at % and on the other hand a slightly higher contamination with nitrogen (1.5 at %). The contamination of Ar in the film is due to the bombardment with Ar+ ions [29]. The amount of Si found for the sample with a flow ratio of 1.0 is around the detection limit. This means that the element is present but the uncertainty in the value is very large. The measured thickness of  $7 \times 10^{18}$  at/cm<sup>2</sup> corresponds to a film thickness of about 640 nm with an assumed density of 1.8 g/cm<sup>3</sup>. For comparison, Kahn [30] found an H-content of 28 at % for a C<sub>2</sub>H<sub>2</sub>/Ar flow ratio of 0.43. There, the higher H-content at lower flow ratio might be due to several effects not specified in [30] like different deposition distance, varying power supplied to the target or different bias voltage at the substrate.

**Table 4.1:** The average chemical composition of the coatings as determined by ERDA.

| Sample | Ar     | Si     | 0      | N      | С      | Н      |
|--------|--------|--------|--------|--------|--------|--------|
|        | [at %] |
| аСН-0  | 0.70   | 0      | 0.11   | 0.87   | 78.8   | 19.5   |
| аСН-2  | 1.49   | 0      | 0.27   | 1.50   | 80.6   | 16.1   |
| аСН-4  | 0.40   | 0      | 0.10   | 0.50   | 78.8   | 20.2   |
| аСН-6  | 0.28   | 0      | 0.09   | 0.38   | 78.8   | 20.5   |
| аСН-8  | 0.06   | 0      | 0.24   | 0.29   | 79.1   | 20.4   |
| аСН-10 | 0.05   | 0.09   | 0.25   | 0.36   | 79.9   | 19.4   |

Figure 4.3 shows the depth profiles of the H-content in all deposited films. The depth resolution for H with about 80 nm is worse than for the other elements because different detection systems had to be used. Therefore, the profile only slowly reaches

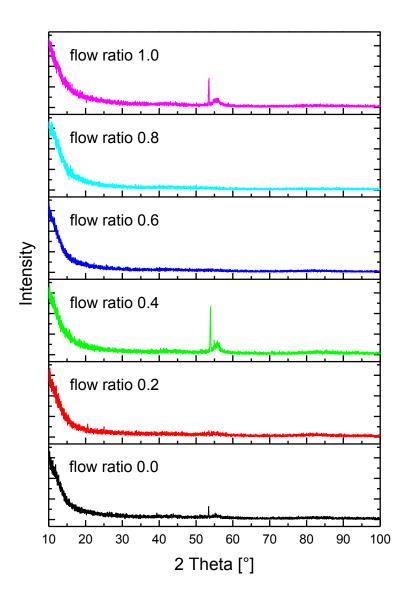
its maximum. The poor depth resolution might also explain the decrease of the H concentration with increasing depth.



**Figure 4.3:** ERDA depth profiles of the H-content for the deposited a-C:H films with different  $C_2H_2/Ar$  flow ratios.

#### 4.3 X-Ray Diffraction

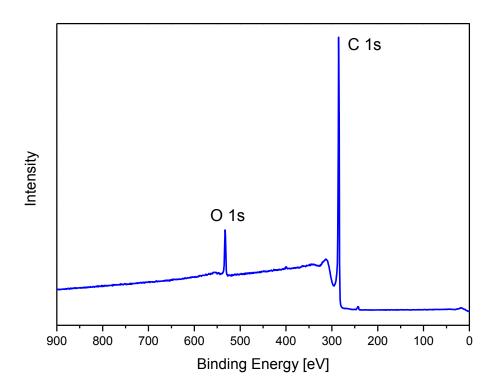
The XRD patterns (Figure 4.4) confirm the expected amorphous structure of the film. It should be noted that the typical graphite peak would appear at about 26° [31]. The sharp peak at about 53° originates from the Si-substrate [31] and the small peak beside results from a slightly tilted angle of incidence. The elevated background at  $2\theta < 20^\circ$  is most probably related to the amorphous film structure and to a partial reflection of the X-ray beam at low detector angles.



**Figure 4.4:** XRD patterns of the amorphous carbon films grown on Si substrates with various  $C_2H_2/Ar$  flow ratios.

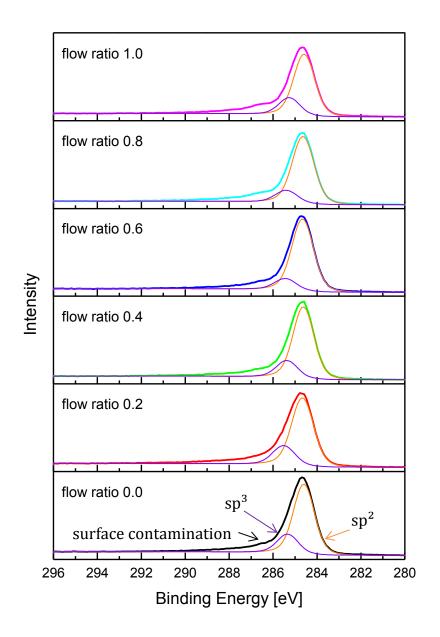
#### 4.4 X-Ray Photoelectron Spectroscopy

The samples were measured as received, without heating process or sputter cleaning to avoid damaging of the chemical bonds. Figure 4.5 shows an exemplary XPS general survey scan of an a-C:H film. It provides information about the present elements in the coating. In this case only carbon (C 1s peak) and negligible oxygen (O 1s peak) were detected. The oxygen might arise from adsorbed water or oxygen picked up during storage at ambient atmosphere [32]. For fitting the C 1s peak at 285 eV, the software UniFit with the Powell fitting algorithm was used to estimate the sp<sup>2</sup> and sp<sup>3</sup> fraction.



**Figure 4.5:** A representative wide XPS scan spectrum showing the oxygen 1s and carbon 1s orbital (sample aCH-0).

Figure 4.6 compares the fitted XPS spectra for all coatings. The sp<sup>2</sup> peak was found at 284.5 and the sp<sup>3</sup> peak at 285.5 eV, which fits well to literature. There, the sp<sup>2</sup> peak shows up at 284.4 and the sp<sup>3</sup> peak at 285.2 eV [6] [33]. The shoulder from 286 to 290 eV is due to surface contamination during storage at ambient atmosphere.

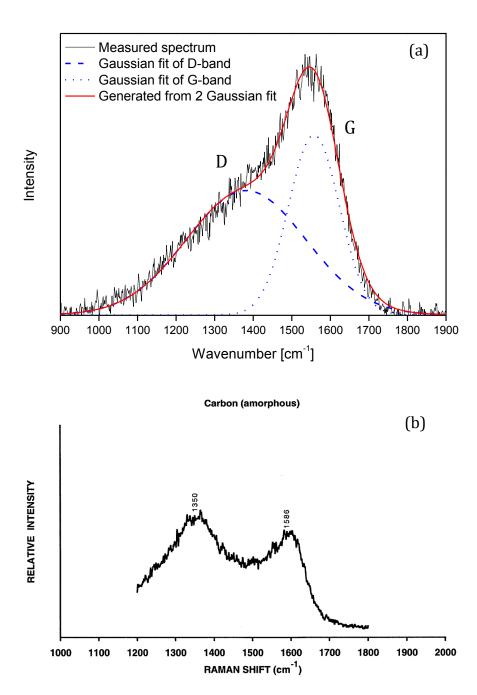


**Figure 4.6:** Fitted XPS spectra of the C 1s peak showing the sp<sup>2</sup> and sp<sup>3</sup> fraction as well as surface contamination.

#### 4.5 Raman Spectroscopy

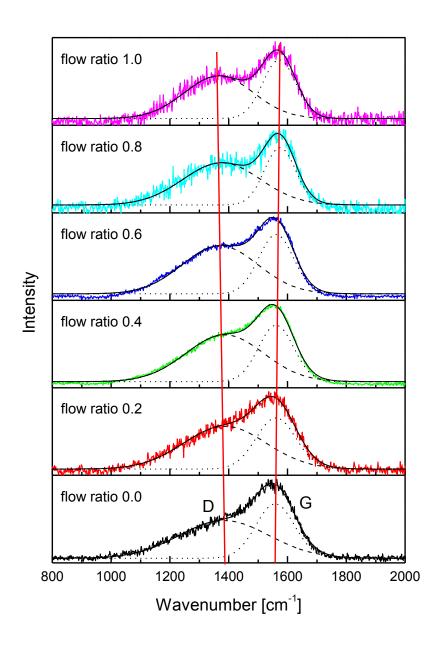
Figure 4.7 (a) shows a Raman spectrum of an amorphous carbon film deposited in pure Ar atmosphere with the Gaussian fits for the D- and G-band. All measured films are characterised by a highly disordered carbon phase. The D-band was found at about 1380 cm<sup>-1</sup> and the G-band at about 1560 cm<sup>-1</sup>. In literature, the positions are given at 1360 and 1560 cm<sup>-1</sup> [16] [34], which fits well.

Compared to literature (Figure 4.7 (b), [35]), the shape of the Raman spectra and the band parameters rather show up an a-C:H structure instead of an a-C structure even if the film is deposited with Ar as sputtering gas only [30]. This can be explained by a relatively high ion energy level because of a low distance between target and substrate [36]. Due to the lower distance, a more intense Ar<sup>+</sup> bombardment can be assumed and the film is more disordered.



**Figure 4.7:** Raman spectrum of (a) a measured amorphous carbon film deposited without reactive gas compared to (b) an amorphous carbon film as reported in [35].

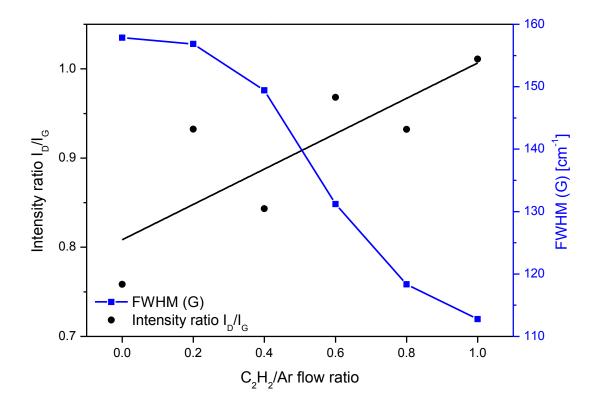
Figure 4.8 compares the deposited films concerning the fitted D- and G-band. It can be observed, that the height of the G-band increases with the  $C_2H_2/Ar$  flow ratio. Furthermore, the G-band slightly moves to higher wavenumbers, simultaneously the D-band moves to lower wavenumbers. In literature, it is mentioned that the clustering of the  $sp^2$  phase mainly affects the peak positions, width and intensity [37]. In principle, the  $sp^2$  clustering can vary independently from the  $sp^3$  content. That means for a given  $sp^3$  content and excitation energy, a number of different Raman spectra, or, equivalently, similar Raman spectra for different  $sp^3$  contents are possible [37].



**Figure 4.8:** Raman spectra of the a-C:H films deposited with different C<sub>2</sub>H<sub>2</sub>/Ar flow ratios.

The interpretation of Raman spectra is quite complex, therefore some guidelines should be noted [16] [38] [34] [39]:

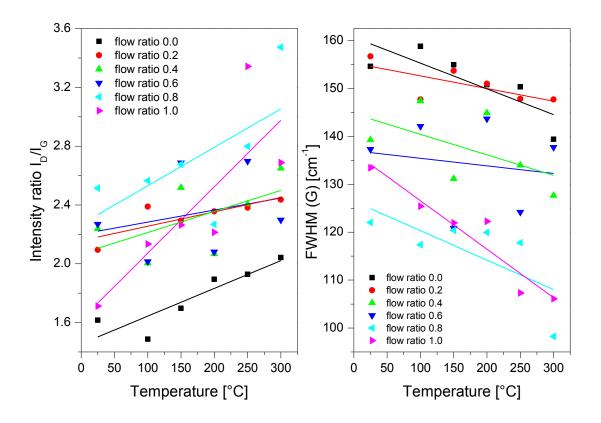
- The G-band of the Raman spectrum taken at visible excitation has its origin in the effect of bond stretching of all carbon atoms in sp<sup>2</sup> hybridisations, both in rings and chains.
- The D-band occurs from the breathing mode of carbon atom rings.
- The ID/IG ratio is an indicator for the sp2 phase organised in rings. A low or nearly zero value of the ID/IG – ratio suggests an sp2 phase organised in chains, whereas a high ID/IG – ratio is a sign of increasing sp2 aromatic rings.
- In the case of a-C:H films, the sp3-hybridisated carbon fraction can be estimated by the Raman parameters. A higher comprehensive (C-C, C-H) sp3 content is related to a low ID/IG ratio.
- The FWHM (G) is used in order to show the trends in the C-C sp3 bonding content. If the FWHM (G) increases in equal measure, the C-C sp3 bonding content increases.



**Figure 4.9:** Intensity ratio  $I_D/I_G$  and FWHM (G) as a function of the  $C_2H_2/Ar$  flow ratio of the deposited films.

Compared to these guidelines, Figure 4.9 can be interpreted as follows: with increasing  $\rm sp^3$  content, the intensity ratio  $\rm I_D/I_G$  increases due to an increasing amount of graphitic rings, while FWHM (G) decreases due to a more ordered structure [40].

Figure 4.10 shows an in situ Raman measurement of the deposited films from room temperature up to 300°C. It can be observed that in general the  $I_D/I_G$  ratio increases for all samples. Equally with increasing flow ratio the  $I_D/I_G$  ratio increases. Simultaneously, FWHM (G) decreases with increasing temperature and with increasing flow ratio the general values of FWHM (G) decrease. Amorphous carbon is known to have a phase transformation above 150°C due to bonded hydrogen liberation [41] [30], which results in increasing size of graphite clusters and affects the  $I_D/I_G$  ratio and FWHM (G).



**Figure 4.10:** In-situ Raman measurements for all deposited films showing the temperature-dependence of the  $I_D/I_G$  ratio and FWHM (G).

### 4.6 Nanoindentation

The measured hardness and Young's modulus of the deposited films are shown in Figure 4.11 as a function of the  $C_2H_2/Ar$  flow ratio. For  $C_2H_2/Ar$  flow ratios above 0.2, the hardness continuously decreases from 25 to 8 GPa and the Young's modulus decreases from about 187 to 55 GPa, respectively. In literature the hardness varies between 10 and 20 GPa for typical a-C:H films with a H-content between 30 and 40 at % [6]. The decrease of the mechanical properties with increasing  $C_2H_2/Ar$  flow ratios is related to a more disordered or even polymeric structure.

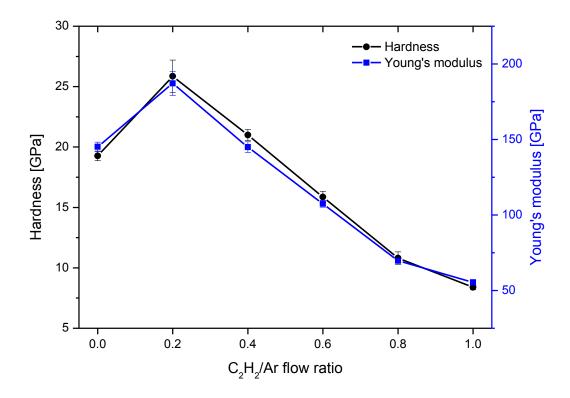
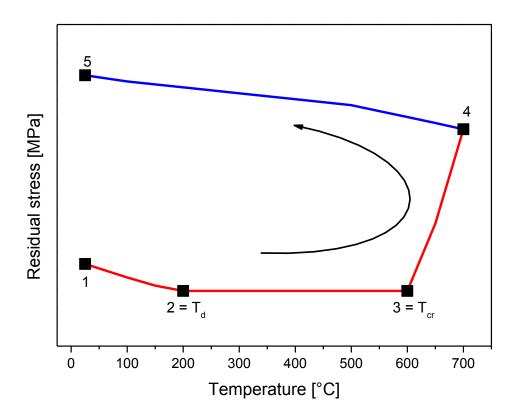


Figure 4.11: Hardness and Young's modulus of the deposited coatings as a function of C<sub>2</sub>H<sub>2</sub>/Ar flow ratio.

### 4.7 Residual Stresses

Figure 4.12 shows a schematic curve of the residual stress in a coating versus temperature. From point 1 to 2, the curve indicates a thermo-elastic behaviour with a low slope due to the similar thermal expansion coefficients  $\alpha$  of the Si-substrate and the a-C:H coating (Si:  $2.6 \times 10^{-6}$  K<sup>-1</sup> [42], graphite:  $1.9 - 2.9 \times 10^{-6}$  K<sup>-1</sup> [43]). Point 2 corresponds to the deposition temperature  $T_d$ . Therefore, a radical change of the

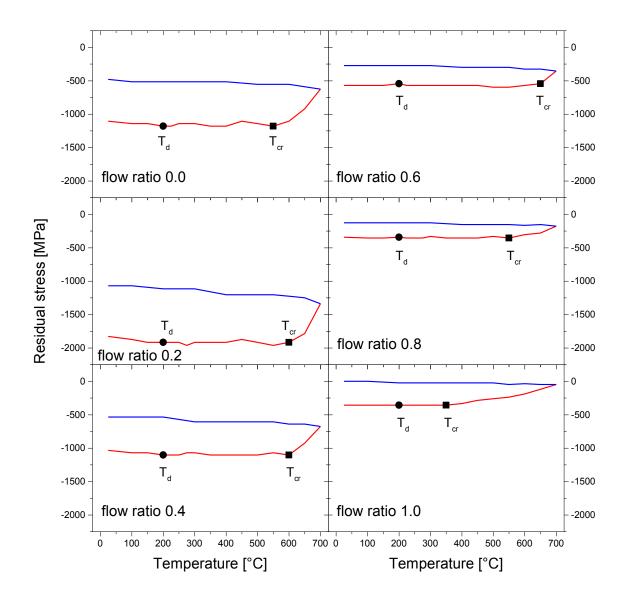
slope would be expected after this point due to structural rearrangements, like healing of point defects. At point 3, which corresponds to the critical temperature  $T_{cr}$ , there is a knee which indicates more dramatic structural changes. For the a-C:H films, there can be a hydrogen liberation or even a transformation from sp<sup>3</sup> to sp<sup>2</sup>. The course of the curve from point 4 to 5 shows a well relaxed behaviour, which is again characterised by thermo-elasticity.



**Figure 4.12:** Schematic curve shape of a residual stress measurement versus temperature showing the key points.

In Figure 4.13, the different coatings are compared concerning the residual stresses during a heating and cooling process. In general, all deposited coatings have stresses that are compressive in nature. It can be observed that the mentioned critical temperature  $T_{cr}$  slightly increases from 550 to 650°C for the coatings with an  $C_2H_2/Ar$  flow ratio from 0.0 to 0.6. The samples grown with flow ratios of 0.8 and 1.0 show an obvious decrease of the critical temperature to 350°C. Furthermore, also the stresses in the as-deposited condition are significantly lower than in those grown at lower flow ratios. These coatings grown at high flow ratios are characterised by a

fully relaxed behaviour after cooling, which corroborates their polymeric behaviour. This could be related to the observed more pronounced graphitic structure, as already mentioned in section 4.5.

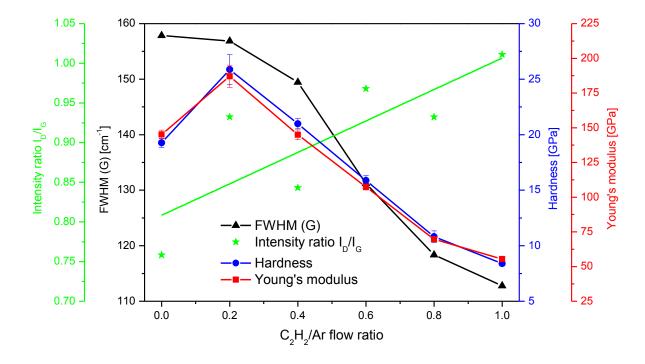


**Figure 4.13:** Coating stress as a function of temperature for the coatings deposited using different  $C_2H_2/Ar$  flow ratios (red: heating, blue: cooling).

## **5** Discussion

# 5.1 Correlation between structural and mechanical properties

Figure 5.1 demonstrates a comparison of the structural information obtained from Raman spectroscopy and the mechanical properties of the coatings. The FWHM (G) is direct proportional to the mechanical properties, like hardness and Young's modulus and indirect proportional to the intensity ratio  $I_D/I_G$  [39]. Therefore, elevated  $C_2H_2$  concentrations in the process gas atmosphere induce an ordering effect in the films as well as a higher degree of polymerisation, which results in a decrease of hardness and Young's modulus [40].



**Figure 5.1:** Comparison of structural information with mechanical properties of the deposited a-C:H films as a function of the  $C_2H_2/Ar$  flow ratio.

# 5.2 Correlation between deposition gas mixture and hydrogen content

As shown in section 4.2, the ERDA measurements yielded an average H-content of about 20 at % for all deposited films. However, due to the variation of the  $C_2H_2/Ar$  flow ratio also a varying H-content would have been expected. Thus, although no

unambiguous answer to this question can be offered within this thesis, some reasons for the nearly unaffected H-content are discussed in the following:

- First of all, a leak in the overall condition of the deposition system could be expected. An indication for this would be a high content of oxygen in the coatings. However, from the results of the ERDA measurements this factor can be excluded, since the average oxygen contamination was below 1 at %.
- A further reason could be a leak within the  $C_2H_2$  mass flow controller, i.e. where the valve does not open and close exactly. Therefore, the possibility could exist that either no or not enough  $C_2H_2$  is added to the deposition gas mixture or that the valve does not close after deposition and additional  $C_2H_2$  might react with the still hot coating. However, it has to be noted, that the brightness and coloration of the plasma intensified with increasing  $C_2H_2/Ar$  flow ratio. The total pressure during deposition increased from  $8 \times 10^{-3}$  to above  $2 \times 10^{-2}$  mbar (see Table 3.1) and also the film growth rate increased (see Figure 4.2). Altogether, this indicates an increasing  $C_2H_2$  content in the deposition gas mixture, since the other deposition parameters like power supply or bias voltage were kept constant. Moreover, the residual pressure of about  $4 \times 10^{-6}$  mbar after deposition speaks against a leak within the mass flow controller.
- The carbon target could have adsorbed water or oxygen out of the atmosphere due to a long storage. However, this would also result in a high contamination of oxygen. Since the target was new and the contamination is below 1 at %, this fact can be excluded as well.
- The deposited samples could absorb water or oxygen out of the atmosphere during storage. However, also in this case a higher content of oxygen would appear in the ERDA results.
- As a last point, which has to be considered, although the mass flow controller was immediately closed at the end of deposition, there could be a residual H-content within the gas background. This is fostered by the fact that hydrogen is the lightest element, which results in the lowest pumping efficiency of the turbomolecular pump [44]. Furthermore, Schneider et al. [45] also explained this phenomenon of hydrogen uptake in amorphous alumina thin films resulting from the high vacuum gas background.

Concluding, it has to be said that further investigations or even recurring deposition runs have to be done to unambiguously clarify the missing correlation between  $C_2H_2/Ar$  flow ratio and H-content.

## 6 CONCLUSION AND OUTLOOK

### 6.1 Conclusion

Within this work, hydrogen containing diamond-like carbon coatings were synthesised by reactive unbalanced magnetron sputtering in an argon/acetylene  $(Ar/C_2H_2)$  atmosphere with  $C_2H_2/Ar$  flow ratios increasing from 0 to 1. The aim was to contribute to the design of biocompatible coatings for medical implants based on magnesium with high H-content and a polymeric structure, to be used as a diffusion barrier between the implant and the surrounding tissue.

The deposited coatings were studied concerning their composition, structure and mechanical properties. The coating thickness varied between 1.4 (without  $C_2H_2$ ) and 2.2 µm ( $C_2H_2$ /Ar flow ratio of 1.0). ERDA measurements yielded an average H-content of about 20 at % and contaminations of oxygen and nitrogen below 1 at %. XRD measurements confirmed the expected amorphous structure of the films. With XPS and Raman spectroscopy the sp² and sp³ fractions were determined, which are directly related to the intensity ratio  $I_D/I_G$ . With increasing  $I_D/I_G$  ratio, the coating structure got more disordered. With an increasing  $C_2H_2$ /Ar flow ratio, the hardness decreased from 25 to 8 GPa and the Young's modulus from 187 to 55 GPa, which indicates an increasing polymeric film structure as well. The residual stress measurements showed compressive stresses for all coatings with different critical temperatures for defect healing processes.

### 6.2 Outlook

This thesis contributes towards the framework conditions for synthesising hydrogenated amorphous carbon films for medical applications. With elevated C<sub>2</sub>H<sub>2</sub>-content, films with even polymeric behaviour can be synthesised. Some ideas for future developments on these films are: To illuminate the bonding structure further, Raman spectroscopy measurements with different wavelengths could be done. Furthermore, transmission electron microscopy (TEM) measurements could give information about the C-H bonding. Next to structural investigations, the a-C:H films could be deposited on magnesium substrates to study the interaction between film and substrate.

On the basis of this diploma thesis, the functionality of the coating system could be further improved. Forward-looking, the amorphous carbon diffusion barrier should on the one hand prevent a temporary magnesium implant from corrosion during a fracture healing process. On the other hand, a slow degradation of the film should ensure a controlled access of water to the magnesium surface due to a specific porosity and for controlled wear of the film. This should provide a controlled degradation of the implant. Next to the corrosion properties, antibacterial additives like silver could be built into the near-surface zone of the coating to avoid an inflammation of the surrounding tissue in the first days after surgery. Moreover, tests in biological solutions (in vitro) and living organism (in vivo) need to be done to further proof the biocompatibility of films based on this concept.

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